





Tools &

Software





CSD18535KTT

SLPS589-MARCH 2016

CSD18535KTT 60 V N-Channel NexFET™ Power MOSFET

1 Features

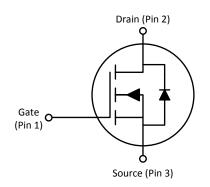
- Ultralow Q_a and Q_{ad}
- Low Thermal Resistance
- Avalanche Rated
- Pb-Free Terminal Plating
- RoHS Compliant
- Halogen Free
- D²PAK Plastic Package

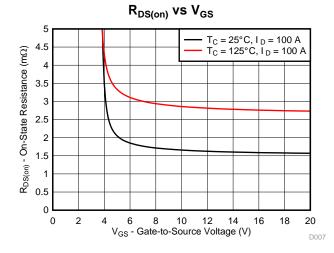
2 Applications

- Secondary Side Synchronous Rectifier
- Motor Control

3 Description

This 60-V, 1.6-m Ω , D²PAK (TO-263) NexFETTM power MOSFET is designed to minimize losses in power conversion applications.





Product Summary

T _A = 25°	C	TYPICAL VA	LUE	UNIT
V _{DS}	Drain-to-Source Voltage	60		V
Qg	Gate Charge Total (10 V)	63	nC	
Q _{gd}	Gate Charge Gate-to-Drain	10.4	nC	
P	Drain-to-Source On-Resistance	V _{GS} = 4.5 V 2.3		mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V 1.6		mΩ
V _{GS(th)}	Threshold Voltage	1.9	V	

Ordering Information⁽¹⁾

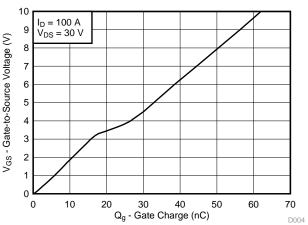
DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18535KTT	500	13-Inch	D ² DAK Plantin Daskans	Tape &
CSD18535KTTT	50	Reel	D ² PAK Plastic Package	Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	±20	V
	Continuous Drain Current (Package limited)	200	А
I _D	Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$	279	А
	Continuous Drain Current (Silicon limited), $T_{C} = 100^{\circ}C$	197	А
I _{DM}	Pulsed Drain Current (1)	400	А
PD	Power Dissipation	300	W
T _J , T _{stg}	Operating Junction and Storage Temperature	-55 to 175	°C
E _{AS}	Avalanche Energy, Single Pulse I_D = 111 A, L = 0.1 mH, R_G = 25 Ω	616	mJ

(1) Max $R_{\theta JC} = 0.5^{\circ}C/W$, pulse duration $\leq 100 \ \mu s$, duty cycle $\leq 1\%$



Gate Charge

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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4 Revision History

DATE	REVISION	NOTES
March 2016	*	Initial release.

5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS				
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _D = 250 μA	60		V
I _{DSS}	Drain-to-source leakage current	$V_{GS} = 0 V, V_{DS} = 48 V$		1	μA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 20 V		100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.4 1.9	2.4	V
D	Drain to course on registerios	V _{GS} = 4.5 V, I _D = 100 A	2.3	2.9	mΩ
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 10 V, I _D = 100 A	1.6	2.0	mΩ
9 _{fs}	Transconductance	V _{DS} = 6 V, I _D = 100 A	263		S
DYNAMI	C CHARACTERISTICS		L		
C _{iss}	Input capacitance		5090	6620	pF
C _{oss}	Output capacitance	V _{GS} = 0 V, V _{DS} = 30 V, <i>f</i> = 1 MHz	890	1150	pF
C _{rss}	Reverse transfer capacitance		24	31	pF
R_{G}	Series gate resistance		0.8	1.6	Ω
Qg	Gate charge total (10 V)		63	81	nC
Q _{gd}	Gate charge gate-to-drain		10.4		nC
Q _{gs}	Gate charge gate-to-source	V _{DS} = 30 V, I _D = 100 A	15.7		nC
Q _{g(th)}	Gate charge at V _{th}		9.4		nC
Q _{oss}	Output charge	V _{DS} = 30 V, V _{GS} = 0 V	140		nC
t _{d(on)}	Turn on delay time		9		ns
t _r	Rise time	V _{DS} = 30 V, V _{GS} = 10 V,	3		ns
t _{d(off)}	Turn off delay time	$I_{\rm DS} = 100 \text{ A}, \text{ R}_{\rm G} = 0 \Omega$	19		ns
t _f	Fall time		3		ns
DIODE C	HARACTERISTICS		f	+	
V_{SD}	Diode forward voltage	I _{SD} = 100 A, V _{GS} = 0 V	0.9	1.0	V
Q _{rr}	Reverse recovery charge	V_{DS} = 30 V, I _F = 100 A,	214		nC
t _{rr}	Reverse recovery time	$di/dt = 300 \text{ A}/\mu\text{s}$	63		ns

5.2 Thermal Information

($T_A = 25^{\circ}C$ unless otherwise stated)

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{ extsf{ heta}JC}$	Junction-to-case thermal resistance			0.5	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance			62	°C/W

0.1

75

50

25

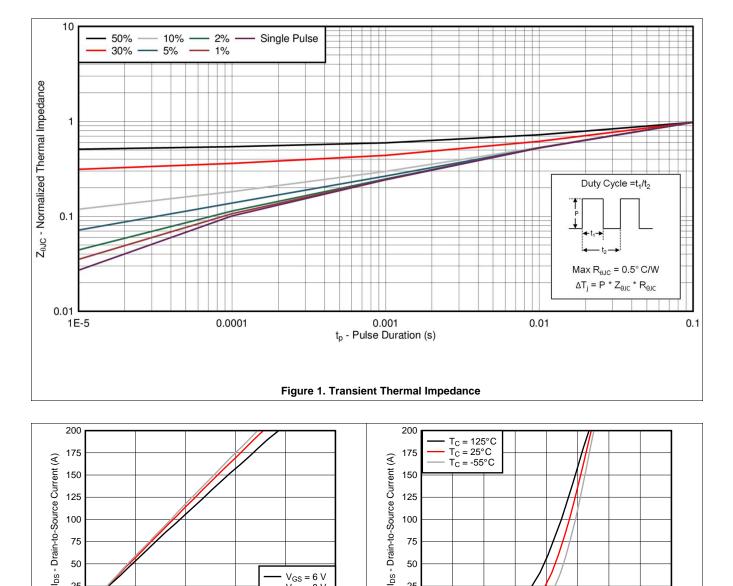
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0

SLPS589-MARCH 2016 5.3 Typical MOSFET Characteristics

CSD18535KTT

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



75

50 - sal

25

0

1

1.5

2

2.5

3

V_{GS} - Gate-to-Source Voltage (V)

Figure 3. Transfer Characteristics

 $V_{DS} = 5 V$

3.5

4

4.5

5

D003

 $V_{GS} = 6 V$

 $V_{GS} = 8 V$ $V_{GS} = 10 V$

0.5

D002

0.4

0.3

V_{DS} - Drain-to-Source Voltage (V)

Figure 2. Saturation Characteristics

0.2

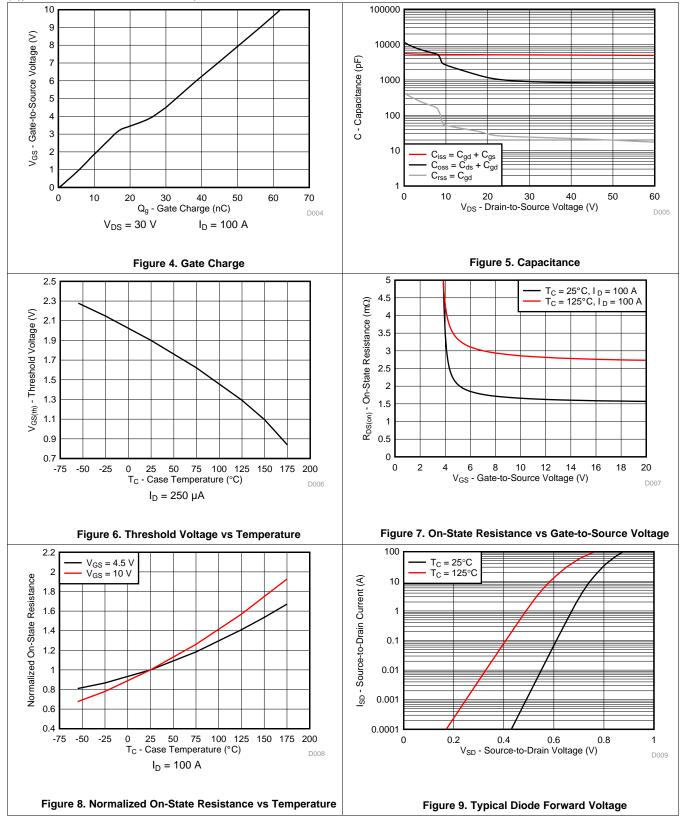


www.ti.com



Typical MOSFET Characteristics (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



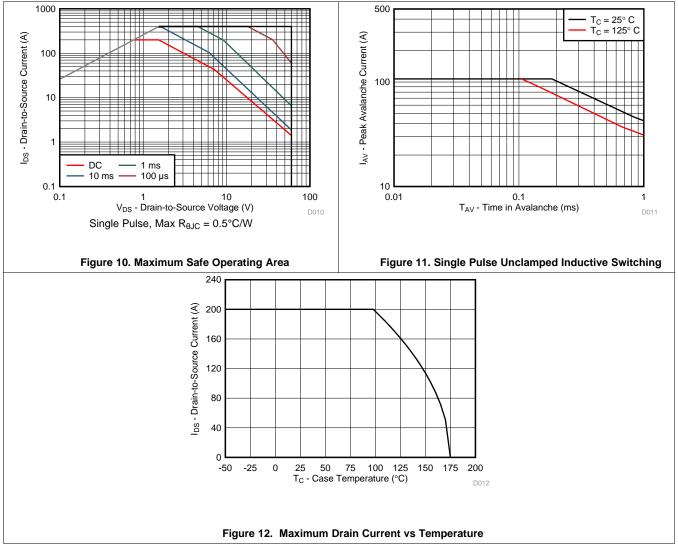


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Typical MOSFET Characteristics (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

NexFET, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

SLYZ022 — TI Glossary.

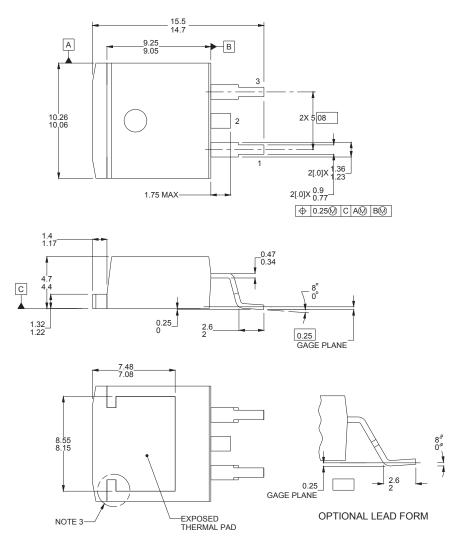
This glossary lists and explains terms, acronyms, and definitions.



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 KTT Package Dimensions



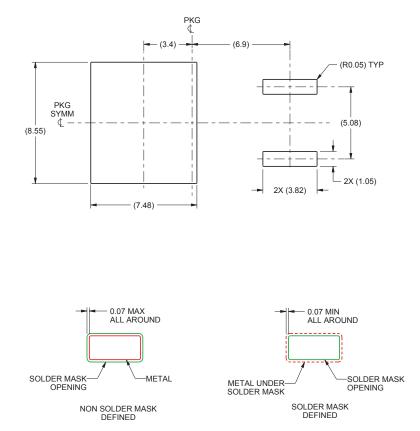
Notes:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. Features may not exist and shape may vary per different assembly sites.

Pin Configuration							
POSITION DESIGNATION							
Pin 1	Gate						
Pin 2 / Tab	Drain						
Pin 3	Source						

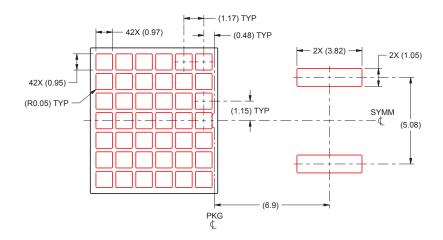


7.2 Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

7.3 Recommended Stencil Opening (0.125 mm Stencil Thickness)



Notes:

- 1. This package is designed to be soldered to a thermal pad on the board. See application notes, *PowerPAD Thermally Enhanced Package* (SLMA002) and *PowerPAD Made Easy* (SLMA004) for more information.
- 2. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 3. Board assembly site may have different recommendations for stencil design.



1-Apr-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD18535KTT	ACTIVE	DDPAK/ TO-263	КТТ	3	500	Pb-Free (RoHS Exempt)	CU SN	Level-2-260C-1 YEAR	-55 to 175	CSD18535KTT	Samples
CSD18535KTTT	ACTIVE	DDPAK/ TO-263	КТТ	3	50	TBD	Call TI	Call TI	-55 to 175		Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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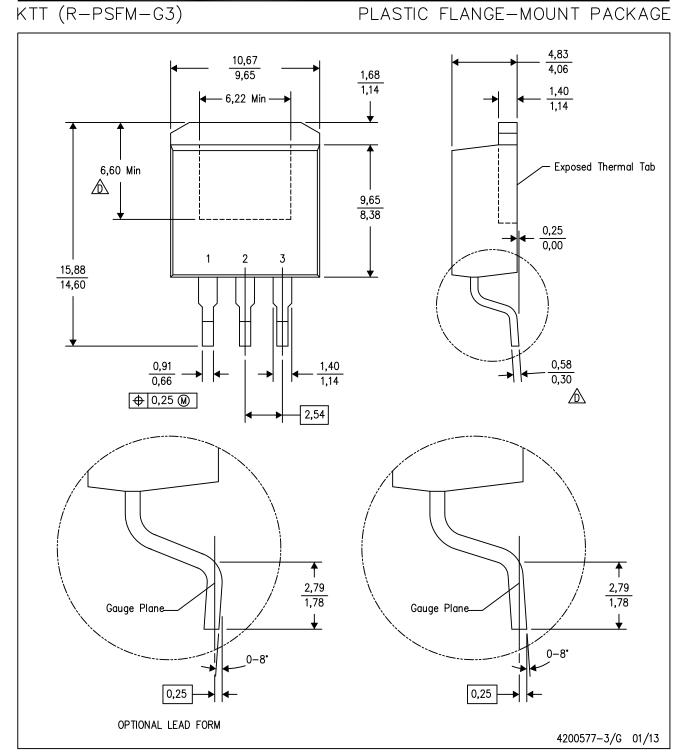


PACKAGE OPTION ADDENDUM

1-Apr-2016

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

MECHANICAL DATA



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion. Mold flash or protrusion not to exceed 0.005 (0,13) per side.

A Falls within JEDEC TO-263 variation AA, except minimum lead thickness and minimum exposed pad length.



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